TOSHIBA Transistor Silicon NPN Epitaxial Type (Darlington Power)

2SD2686

Solenoid Drive Applications Motor Drive Applications

- High DC current gain: $h_{FE} = 2000$ (min) ($V_{CE} = 2$ A, $I_{C} = 1$ A)
- Zener diode included between collector and base

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	50	٧	
Collector-emitter voltage		V _{CEO}	60±10	٧	
Emitter-base voltage		V _{EBO}	8	V	
Collector current	DC	IC	1	Α	
	Pulse	I _{CP}	3		
Base current		ΙΒ	0.5	Α	
Collector power dissipation	DC	P _C (Note 1)	1.0	W	
	t = 10 s	FC (Note 1)	2.5		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

Note 1: Mounted on an FR4 board (glass-epoxy; 1.6 mm thick; Cu area, $645~\text{mm}^2$)

Unit: mm

4.6 MAX

1.6 MAX

1.7 MAX

1.6 MAX

1.7 MAX

1.6 MAX

1.7 MAX

1.8 MAX

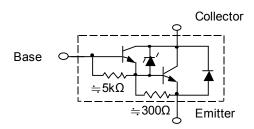
1.

Weight: 0.05 g (typ.)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

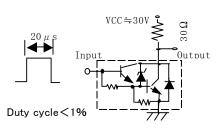
Equivalent Circuit



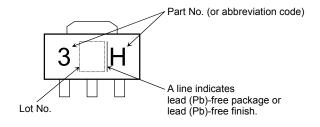
Electrical Characteristics (Ta = 25°C)

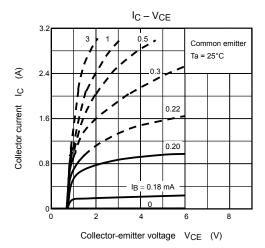
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cutoff current		I _{CBO}	$V_{CB} = 45 \text{ V}, I_E = 0$	_	_	10	μА
		ICEO	V _{CE} = 45 V, I _E = 0	_	_	10	μА
Emitter cutoff current		I _{EBO}	$V_{EB} = 8 \text{ V}, I_{C} = 0$	0.80	_	4.0	mA
Collector-emitter breakdown voltage		V (BR) CEO	$I_C = 10 \text{ mA}, I_B = 0$	50	60	70	V
DC current gain		h _{FE}	V _{CE} = 2 V, I _C = 1.0 A	2000	_	_	
Collector-emitter saturation voltage		VCE (sat) (1)	I _C = 0.5 A, I _B = 1 mA	_	_	1.2	V
		V _{CE} (sat) (2)	I _C = 1.0 A, I _B = 1 mA	_	_	1.5	V
Base-emitter saturation voltage		V _{BE (sat)}	I _C = 1.0 A, I _B = 1 mA	_	_	2.0	V
Switching time	Rise time	t _{on}	See Figure 1 circuit diagram.	_	0.4	_	μ\$
	Storage time	t _{stg}		_	4.0	_	
	Fall time	t _f	VCC = 30 V, NL = 30 Ω	_	0.6	_	

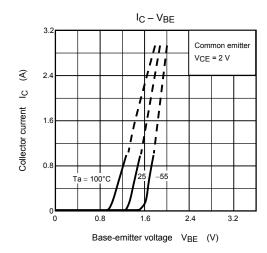
Figure 1. Switching Time Test Circuit & Timing Chart

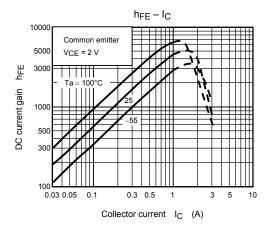


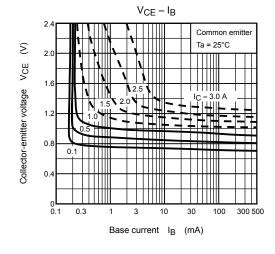
Marking

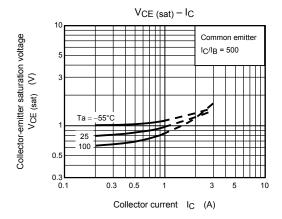


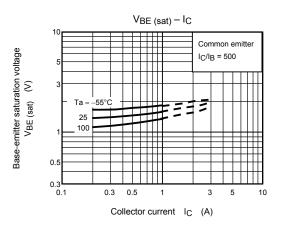




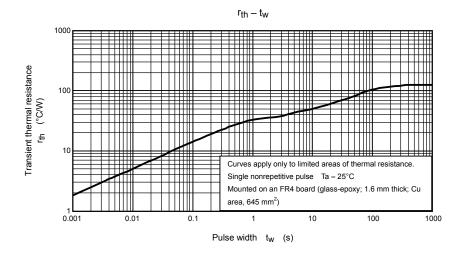


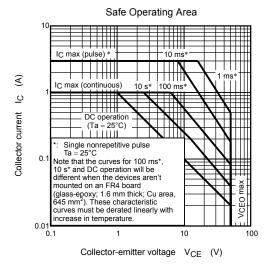






3 2006-11-21





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5 2006-11-21